3501 ED BLUESTEIN BLVD., AUSTIN, TEXAS 78721

MCM6810

128 × 8-BIT STATIC RANDOM ACCESS MEMORY

The MCM6810 is a byte-organized memory designed for use in busorganized systems. It is fabricated with N-channel silicon-gate technology. For ease of use, the device operates from a single power supply, has compatibility with TTL and DTL, and needs no clocks or refreshing because of static operation.

The memory is compatible with the M6800 Microcomputer Family, providing random storage in byte increments. Memory expansion is provided through multiple Chip Select inputs.

- Organized as 128 Bytes of 8 Bits
- Static Operation
- Bidirectional Three-State Data Input/Output
- Six Chip Select Inputs (Four Active Low, Two Active High)
- Single 5-Volt Power Supply
- TTL Compatible
- Maximum Access Time = 450 ns − MCM6810

360 ns - MCM68A10

250 ns - MCM68B10

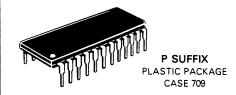
ORDERING INFORMATION

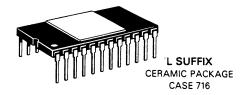
Package Type	Frequency (MHz)	Temperature	Order Number
Ceramic	1.0	0°C to 70°C	MCM6810L
L Suffix	1.0	-40°C to 85°C	MCM6810CL
	1.5	0°C to 70°C	MCM68A10L
	1.5	-40°C to 85°C	MCM68A10CL
	2.0	0°C to 70°C	MCM68B10L
Plastic	1.0	0°C to 70°C	MCM6810P
P Suffix	1.0	– 40°C to 85°C	MCM6810CP
	1.5	0°C to 70°C	MCM68A10P
	1.5	– 40°C to 85°C	MCM68A10CP
	2.0	0°C to 70°C	MCM68B10P
Cerdip	1.0	0°C to 70°C	MCM6810S
S Suffix	1.0	-40°C to 85°C	MCM6810CS
	1.5	0°C to 70°C	MCM68A10S
	1.5	-40°C to 85°C	MCM68A10CS
	2.0	0°C to 70°C	MCM68B10S

MOS

(N-CHANNEL, SILICON-GATE)

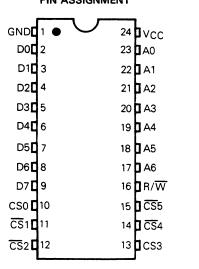
128×8-BIT STATIC RANDOM ACCESS MEMORY



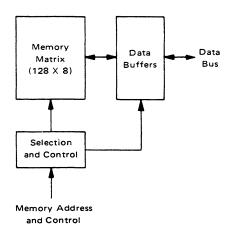




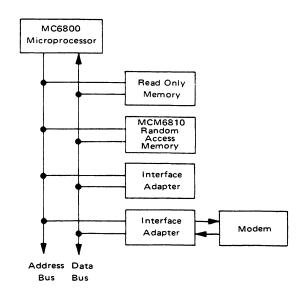
PIN ASSIGNMENT



MCM6810 RANDOM ACCESS MEMORY BLOCK DIAGRAM



M6800 MICROCOMPUTER FAMILY BLOCK DIAGRAM



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	Vcc	-0.3 to $+7.0$	٧
Input Voltage	V _{in}	-0.3 to $+7.0$	٧
Operating Temperature Range MCM6810, MCM68A10, MCM68B10 MCM6810C, MCM68A10C	ТА	T _L to T _H 0 to +70 -40 to +85	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage (e.g., either VSS or VCC).

THERMAL CHARACTERISTICS

Characteristics	Symbol	Value	Unit
Thermal Resistance			
Ceramic		60	
Plastic	$\theta_{ m JA}$	120	°C/W
Cerdip		65	

POWER CONSIDERATIONS

The average chip-junction temperature, T.J., in °C can be obtained from:

$$T_{J} = T_{A} + (P_{D}.\theta_{JA}) \tag{1}$$

Where:

T_A ≡ Ambient Temperature, °C

θ_{JA}≡Package Thermal Resistance, Junction-to-Ambient, °C/W

PD≡PINT+PPORT

 $P_{INT} = I_{CC} \times V_{CC}$, Watts - Chip Internal Power

PPORT≡Port Power Dissipation, Watts — User Determined

For most applications PPORT ≪PINT and can be neglected. PPORT may become significant if the device is configured to drive Darlington bases or sink LED loads.

An approximate relationship between PD and TJ (if PPORT is neglected) is:

$$P_D = K \div (T_J + 273^{\circ}C) \tag{2}$$

Solving equations 1 and 2 for K gives:

 $K = PD^{\bullet}(T_A + 273^{\circ}C) + \theta_{JA} \bullet PD^2$ (3)

Where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A . Using this value of K the values of P_D and T_J can be obtained by solving equations (1) and (2) iteratively for any value of T_A .

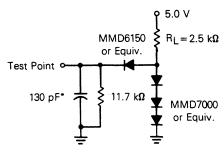


BLOCK DIAGRAM D0 D1 A0 A1 23 22 D2 D3 D4 D5 D6 D7 Memory A2 A3 21 · 3-State Address Matrix Buffer Decode (128×8) 19 Α5 18 8 A6 17 <u>CS</u>5 <u>CS</u>4 15 14 . Memory CS3 13 Control CS2 12 $V_{CC} = Pin 24$ GND = Pin 1CS1 11 CS0 10-16 Read/Write

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0 \text{ Vdc } \pm 5\%$, $V_{SS} = 0$, $T_A = T_L$ to T_H unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
Input High Voltage		VIH	V _{SS} + 2.0	Vcc	V
Input Low Voltage		VIL	V _{SS} -0.3	V _{SS} +0.8	V
Input Current (A _n , R/ \overline{W} , \overline{CS}_n) (V _{in} =0 to 5.25 V)		lin		2.5	μΑ
Output High Voltage ($I_{OH} = -205 \mu A$)		∨он	2.4	-	V
Output Low Voltage (IOL=1.6 mA)		VOL	_	0.4	V
Output Leakage Current (Three-State) (CS = 0.8 V or \overline{CS} = 2.0 V, V _{out} = 0.4 V	/ to 2.4 V)	^I TSI	_	10	μΑ
Supply Current	1.0 MHz		_	80	mA
(V _{CC} =5.25 V, All Other Pins Grounded)	1.5, 2.0 MHz	1CC		100	11174
Input Capacitance (A _n , R/ \overline{W} , CS _n , \overline{CS}_n) (V _{in} =0, T _A =25°C, f=1.0 MHz)		Cin	_	7.5	рF
Output Capacitance (D _n) ($V_{out}=0$, $T_A=25$ °C, $f=1.0$ MHz, $CSO=0$)		C _{out}	_	12.5	рF

AC TEST LOAD



*Includes Jig Capacitance

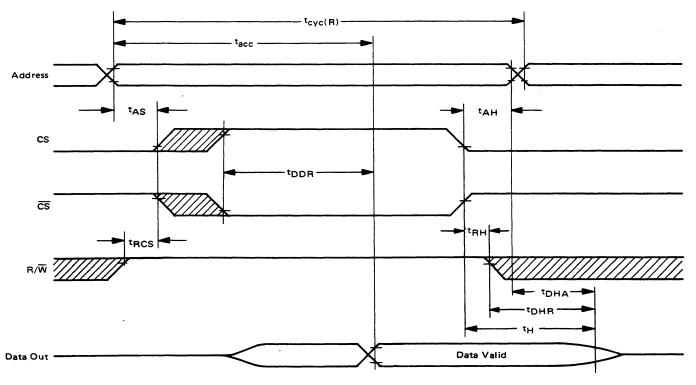


AC OPERATING CONDITIONS AND CHARACTERISTICS

READ CYCLE ($V_{CC} = 5.0 \text{ V} \pm 5\%$, $V_{SS} = 0$, $T_A = T_L$ to T_H unless otherwise noted.)

		MCM	16810	мсм	68A10	MCM	68B10	
Characteristic	Symbol	Min	Max	Min	Max	Min	Max	Unit
Read Cycle Time	t _{cyc} (R)	450	_	360	_	250	_	ns
Access Time	tacc	T -	450	_	360		250	ns
Address Setup Time	^t AS	20	-	20	_	20		ns
Address Hold Time	^t AH	0	_	0	_	0	_	ns
Data Delay Time (Read)	†DDR	-	230	_	220	_	180	ns
Read to Select Delay Time	tRCS	0	_	0	_	0	-	ns
Data Hold from Address	tDHA	10	_	10	_	10	_	ns
Output Hold Time	tн	10	_	10	-	10	_	ns
Data Hold from Read	^t DHR	10	80	10	60	10	60	ns
Read Hold from Chip Select	^t RH	0		0	_	0	_	ns

READ CYCLE TIMING



- Voltage levels shown are V_L≤0.4 V, V_H≥2.4 V, unless otherwise specified.
 Measurement points shown are 0.8 V and 2.0 V, unless otherwise specified.
- 3. CS and $\overline{\text{CS}}$ have same timing.

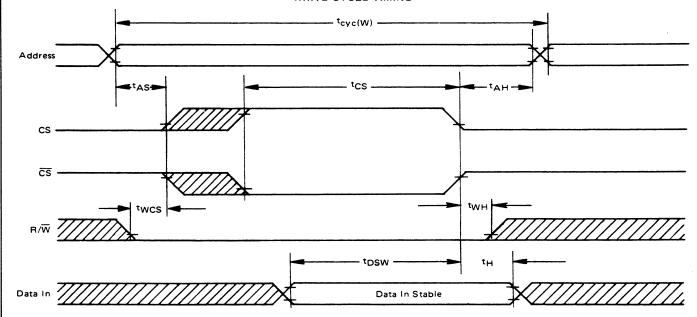




WRITE CYCLE (V_{CC} = 5.0 V \pm 5%, V_{SS} = 0, T_A = T_L to T_H unless otherwise noted.)

		MCM6810		MCM68A10		MCM68B10		
Characteristic	Symbol	Min	Max	Min	Max	Min	Max	Unit
Write Cycle Time	t _{cyc} (W)	450	-	360	_	250	_	ns
Address Setup Time	^t AS	20	_	20	_	20	-	ns
Address Hold Time	^t AH	0	-	0		0	_	ns
Chip Select Pulse Width	tcs	300	-	250	-	210		ns
Write to Chip Select Delay Time	twcs	0	-	0	_	0		ns
Data Setup Time (Write)	^t DSW	190	-	80	_	60	_	ns
Input Hold Time	tн	10	-	10		10	-	ns
Write Hold Time from Chip Select	tWH	0	_	0		0	_	ns

WRITE CYCLE TIMING



NOTES:

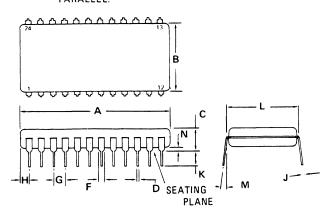
- 1. Voltage levels shown are $V_L \le 0.4 \text{ V}$, $V_H \ge 2.4 \text{ V}$, unless otherwise specified. 2. Measurement points shown are 0.8 V and 2.0 V, unless otherwise specified.
- 3. CS and $\overline{\text{CS}}$ have same timing.





PACKAGE DIMENSIONS

- 1. LEADS, TRUE POSITIONED WITHIN 0.25 mm (0.010) DIA AT SEATING PLANE AT MAXIMUM MATERIAL CON DITION. (DIM. "D") 2. DIM "L" TO CENTER OF LEADS WHEN FORMED
- PARALLEL.

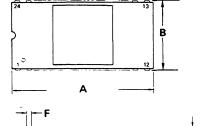


CASE 709-02 (PLASTIC)

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	31.37	32.13	1.235	1.265
В	13.72	14.22	0.540	0.560
C	4.57	5.08	0.180	0.200
D	0.36	0.51	0.014	0.020
F	1.02	1.52	0.040	0.060
G	2.41	2.67	0.095	0.105
H	1.78	2.03	0.070	0.080
J	0.20	0.30	0.008	0.012
K	3.05	3.56	0.120	0.140
L	14.73	15.24	0.580	0.600
M	00	10 ⁰	00	10 ⁰
N	0.51	1.02	0.020	0.040

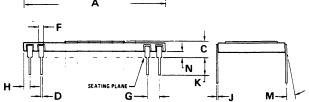
CASE 716-06

(CERAMIC)

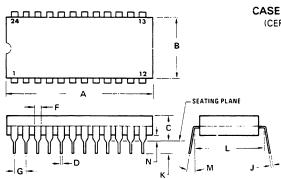


NOTE:

1. LEADS TRUE POSITIONED WITHIN 0.25mm (0.010) DIA (AT SEATING PLANE) AT MAXIMUM MATERIAL CONDITION.



	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	29.97	30.99	1.180	1.220	
В	14.88	15.62	0.585	0.615	
C	3.05	4.19	0.120	0.165	
D	0.38	0.53	0.015	0.021	
F	0.76	1.40	0.030	0.055	
G	2.54	BSC	0.100 BSC		
Н	0.76	1.78	0.030	0.070	
J	0.20	0.30	800.0	0.012	
K	2.54	4.19	0.100	0.165	
L	14.88	15.37	0.585	0.605	
M		10°	-	10 ⁰	
N	0.51	1.52	0.020	0.060	



CASE 623-03

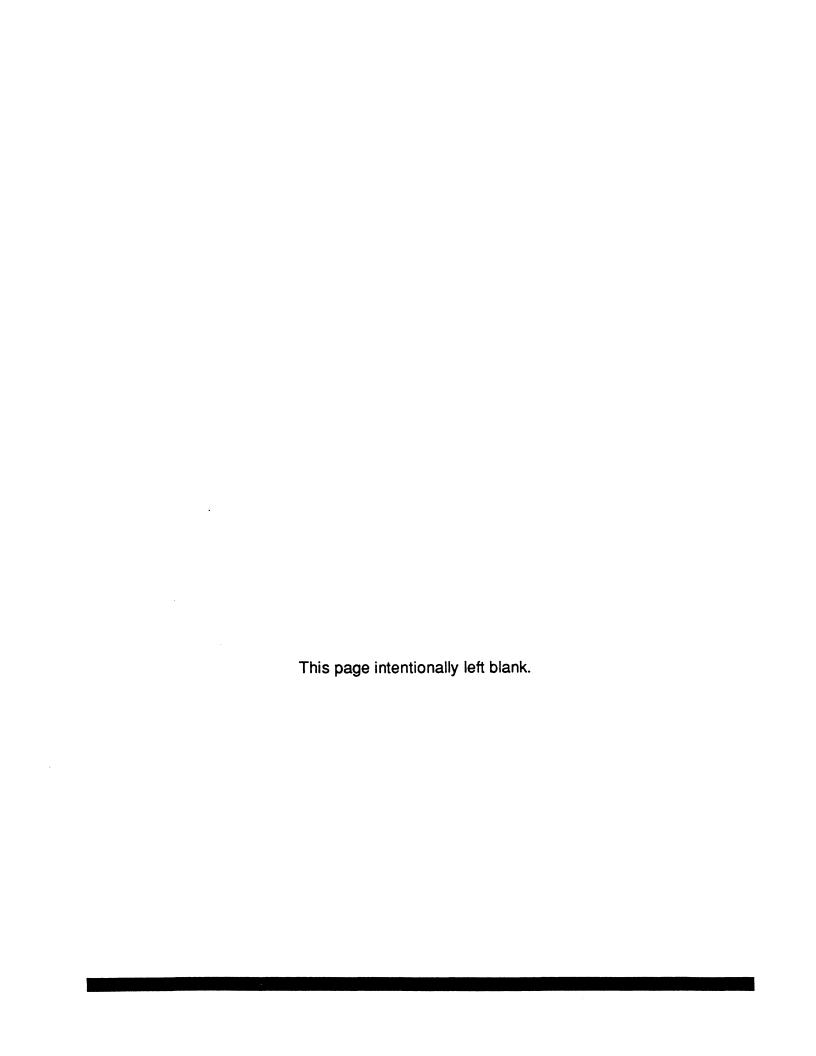
(CERDIP)

	MILLIN	RETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
А	31.24	32.77	1.230	1.290	
В	12.70	15.49	0.500	0.610	
C	4.06	5.59	0.160	0.220	
D	0.41	0.51	0.016	9.020	
F	1.27	1.52	0.050	0.060	
G	2.54	2.54 BSC 0.1		BSC	
J	0.20	0.30	0.008	0.012	
K	2.29	4.06	0.090	0.160	
L	15.24 BSC		0.600	BSC	
M	Oo	15 ⁰	00	15 ⁰	
N	0.51	1.27	0.020	0.050	

NOTES:

- 1. DIM "L" TO CENTER OF LEADS WHEN FORMED
- PARALLEL. 2. LEADS WITHIN 0.13 mm (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION. (WHEN FORMED PARALLEL)





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